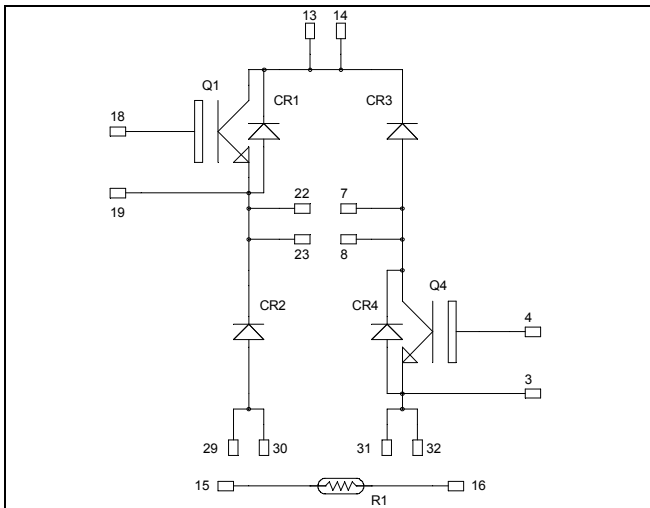


## Asymmetrical - Bridge NPT IGBT Power Module

$V_{CES} = 1200V$   
 $I_C = 50A @ T_c = 80^\circ C$

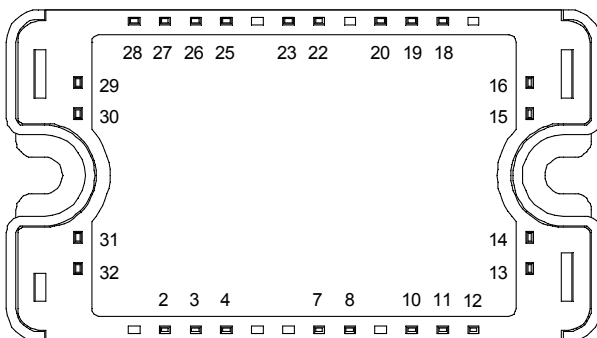


### Application

- AC and DC motor control
- Switched Mode Power Supplies

### Features

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Symmetrical design
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring



### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive TC of VCEsat
- RoHS compliant

All multiple inputs and outputs must be shorted together  
 Example: 13/14 ; 29/30 ; 22/23 ...

### Absolute maximum ratings

| Symbol    | Parameter                             | Max ratings         | Unit         |
|-----------|---------------------------------------|---------------------|--------------|
| $V_{CES}$ | Collector - Emitter Breakdown Voltage | 1200                | V            |
| $I_C$     | Continuous Collector Current          | $T_c = 25^\circ C$  | 70           |
|           |                                       | $T_c = 80^\circ C$  | 50           |
| $I_{CM}$  | Pulsed Collector Current              | $T_c = 25^\circ C$  | 150          |
| $V_{GE}$  | Gate - Emitter Voltage                | $\pm 20$            | V            |
| $P_D$     | Maximum Power Dissipation             | $T_c = 25^\circ C$  | 312          |
| RBSOA     | Reverse Bias Safe Operating Area      | $T_j = 150^\circ C$ | 100A @ 1200V |

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

| Symbol        | Characteristic                       | Test Conditions                                 | Min                       | Typ | Max | Unit          |
|---------------|--------------------------------------|---|---------------------------|-----|-----|---------------|
| $I_{CES}$     | Zero Gate Voltage Collector Current  | $V_{GE} = 0\text{V}$<br>$V_{CE} = 1200\text{V}$ | $T_j = 25^\circ\text{C}$  |     | 250 | $\mu\text{A}$ |
|               |                                      |   | $T_j = 125^\circ\text{C}$ |     | 500 |               |
| $V_{CE(sat)}$ | Collector Emitter saturation Voltage | $V_{GE} = 15\text{V}$<br>$I_C = 50\text{A}$     | $T_j = 25^\circ\text{C}$  | 3.2 | 3.7 | V             |
|               |                                      |   | $T_j = 125^\circ\text{C}$ | 4.0 |     |               |
| $V_{GE(th)}$  | Gate Threshold Voltage               | $V_{GE} = V_{CE}, I_C = 1\text{mA}$             | 4.5                       |     | 6.5 | V             |
| $I_{GES}$     | Gate – Emitter Leakage Current       | $V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$       |                           |     | 100 | nA            |

**Dynamic Characteristics**

| Symbol       | Characteristic               | Test Conditions  | Min                       | Typ  | Max  | Unit |
|--------------|------------------------------|--|---------------------------|------|------|------|
| $C_{ies}$    | Input Capacitance            | $V_{GE} = 0\text{V}$<br>$V_{CE} = 25\text{V}$<br>$f = 1\text{MHz}$   |                           | 3450 |      | pF   |
| $C_{oes}$    | Output Capacitance           |  |                           | 330  |      |      |
| $C_{res}$    | Reverse Transfer Capacitance |  |                           | 220  |      |      |
| $Q_g$        | Total gate Charge            | $V_{GS} = 15\text{V}$<br>$V_{Bus} = 600\text{V}$<br>$I_C = 50\text{A}$   |                           | 330  |      | nC   |
| $Q_{ge}$     | Gate – Emitter Charge        |  |                           | 35   |      |      |
| $Q_{gc}$     | Gate – Collector Charge      |  |                           | 200  |      |      |
| $T_{d(on)}$  | Turn-on Delay Time           | Inductive Switching ( $25^\circ\text{C}$ )<br>$V_{GE} = 15\text{V}$<br>$V_{Bus} = 600\text{V}$<br>$I_C = 50\text{A}$<br>$R_G = 5\ \Omega$      |                           | 35   |      | ns   |
| $T_r$        | Rise Time                    |  |                           | 65   |      |      |
| $T_{d(off)}$ | Turn-off Delay Time          |  |                           | 320  |      |      |
| $T_f$        | Fall Time                    |  |                           | 30   |      |      |
| $T_{d(on)}$  | Turn-on Delay Time           | Inductive Switching ( $125^\circ\text{C}$ )<br>$V_{GE} = \pm 15\text{V}$<br>$V_{Bus} = 600\text{V}$<br>$I_C = 50\text{A}$<br>$R_G = 5\ \Omega$ |                           | 35   |      | ns   |
| $T_r$        | Rise Time                    |  |                           | 65   |      |      |
| $T_{d(off)}$ | Turn-off Delay Time          |  |                           | 360  |      |      |
| $T_f$        | Fall Time                    |  |                           | 40   |      |      |
| $E_{on}$     | Turn-on Switching Energy     | $V_{GE} = \pm 15\text{V}$<br>$V_{Bus} = 600\text{V}$<br>$I_C = 50\text{A}$<br>$R_G = 5\ \Omega$  | $T_j = 125^\circ\text{C}$ |      | 6.9  | mJ   |
| $E_{off}$    | Turn-off Switching Energy    |  |                           |      | 3.05 |      |
| $I_{sc}$     | Short Circuit data           | $V_{GE} \leq 15\text{V}; V_{Bus} = 900\text{V}$<br>$t_p \leq 10\ \mu\text{s}; T_j = 125^\circ\text{C}$   |                           | 300  |      | A    |

**Diode ratings and characteristics (CR2 & CR3)**

| Symbol    | Characteristic                          | Test Conditions  | Min                       | Typ  | Max | Unit          |
|-----------|---|--|---------------------------|------|-----|---------------|
| $V_{RRM}$ | Maximum Peak Repetitive Reverse Voltage |  | 1200                      |      |     | V             |
| $I_{RM}$  | Maximum Reverse Leakage Current         | $V_R = 1200\text{V}$   | $T_j = 25^\circ\text{C}$  |      | 100 | $\mu\text{A}$ |
|           |   |  | $T_j = 125^\circ\text{C}$ |      | 500 |               |
| $I_F$     | DC Forward Current                      | $T_C = 80^\circ\text{C}$   |                           | 60   |     | A             |
| $V_F$     | Diode Forward Voltage                   | $I_F = 60\text{A}$   |                           | 2.5  | 3   | V             |
|           |   | $I_F = 120\text{A}$  |                           | 3    |     |               |
|           |   | $I_F = 60\text{A}$   | $T_j = 125^\circ\text{C}$ | 1.8  |     |               |
| $t_{rr}$  | Reverse Recovery Time                   | $I_F = 60\text{A}$<br>$V_R = 800\text{V}$<br>$di/dt = 200\text{A}/\mu\text{s}$ | $T_j = 25^\circ\text{C}$  | 265  |     | ns            |
|           |   |  | $T_j = 125^\circ\text{C}$ | 350  |     |               |
| $Q_{rr}$  | Reverse Recovery Charge                 | $I_F = 60\text{A}$<br>$V_R = 800\text{V}$<br>$di/dt = 200\text{A}/\mu\text{s}$ | $T_j = 25^\circ\text{C}$  | 560  |     | nC            |
|           |   |  | $T_j = 125^\circ\text{C}$ | 2890 |     |               |

CR1 &amp; CR4 are IGBT protection diodes only

## Thermal and package characteristics

| Symbol            | Characteristic   | Min         | Typ | Max | Unit |     |
|-------------------|--|-------------|-----|-----|------|-----|
| R <sub>thJC</sub> | Junction to Case Thermal Resistance                          | IGBT        |     | 0.4 | °C/W |     |
|                   |  | Diode       |     | 0.9 |      |     |
| V <sub>ISOL</sub> | RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz | 4000        |     |     | V    |     |
| T <sub>J</sub>    | Operating junction temperature range                         | -40         |     | 150 | °C   |     |
| T <sub>STG</sub>  | Storage Temperature Range                                    | -40         |     | 125 |      |     |
| T <sub>C</sub>    | Operating Case Temperature                                   | -40         |     | 100 |      |     |
| Torque            | Mounting torque  | To heatsink | M4  | 2   | 3    | N.m |
| Wt                | Package Weight   |             |     |     | 110  | g   |

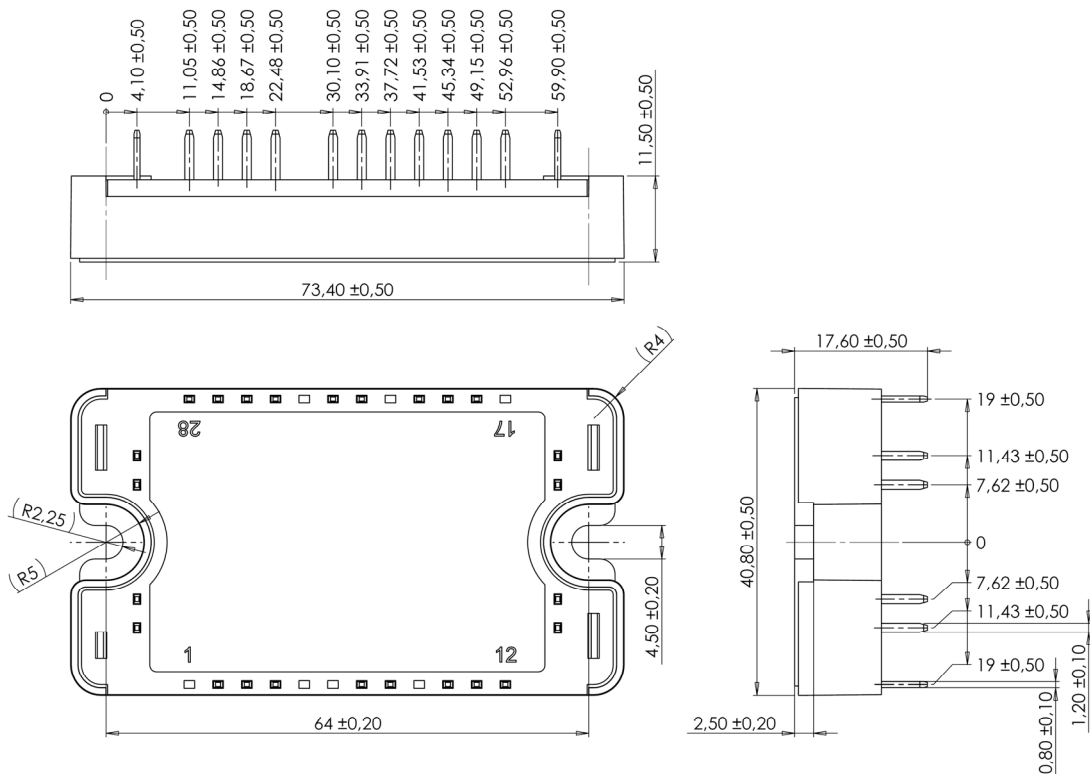
## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

| Symbol                            | Characteristic             | Min                   | Typ  | Max | Unit |
|-----------------------------------|----------------------------|-----------------------|------|-----|------|
| R <sub>25</sub>                   | Resistance @ 25°C          |                       | 50   |     | kΩ   |
| ΔR <sub>25</sub> /R <sub>25</sub> |                            |                       | 5    |     | %    |
| B <sub>25/85</sub>                | T <sub>25</sub> = 298.15 K |                       | 3952 |     | K    |
| ΔB/B                              |                            | T <sub>C</sub> =100°C | 4    |     | %    |

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

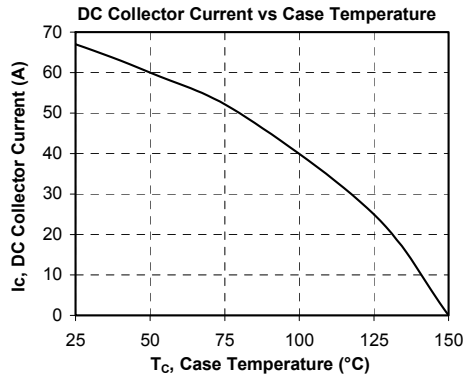
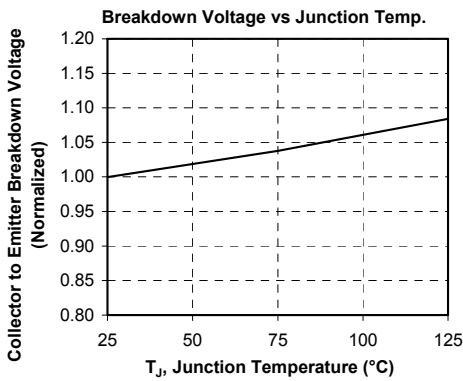
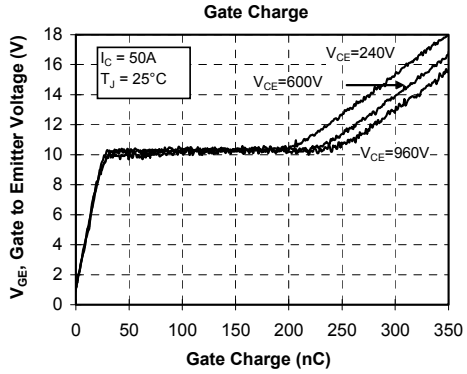
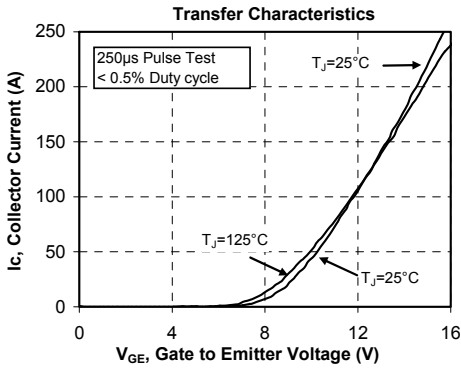
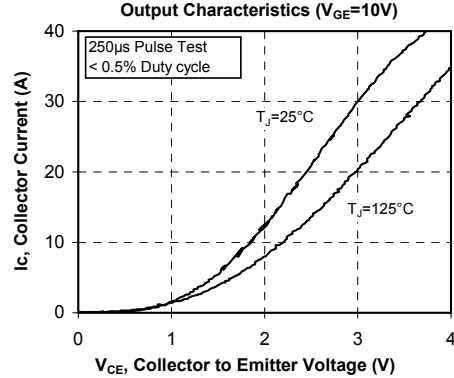
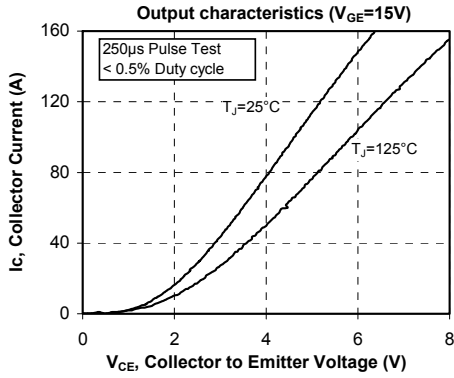
T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

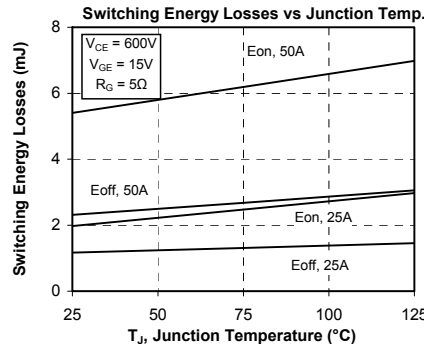
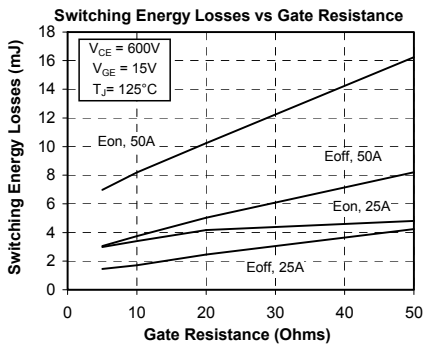
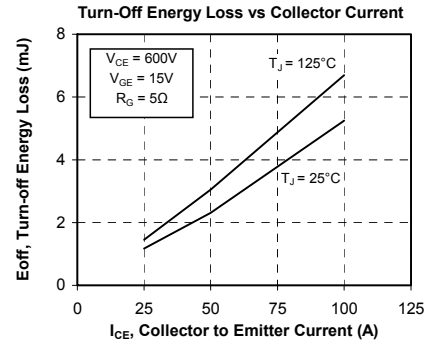
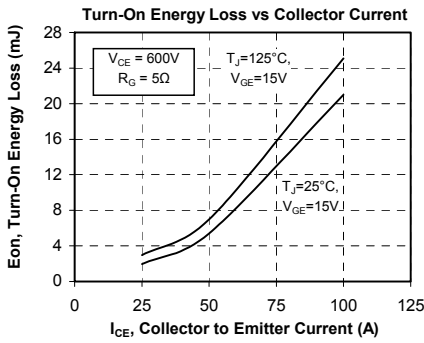
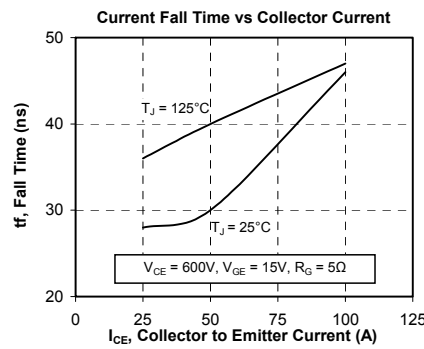
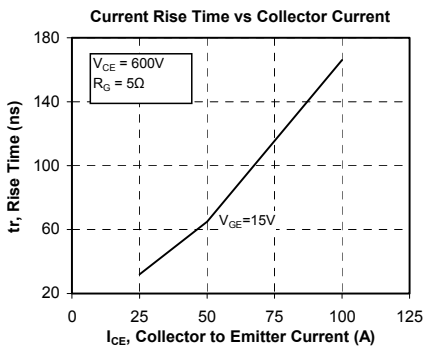
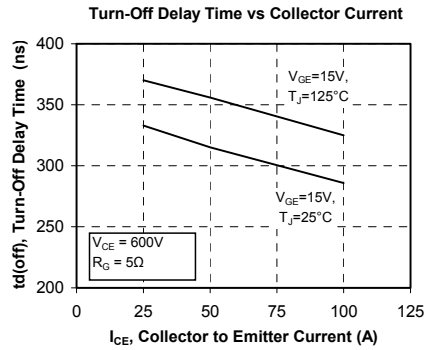
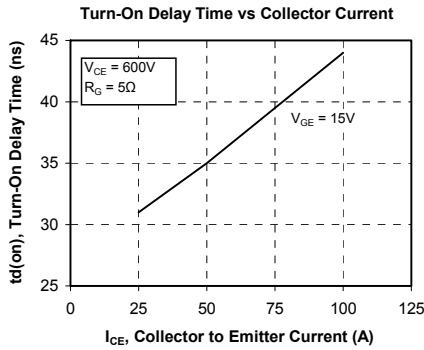
## SP3 Package outline (dimensions in mm)

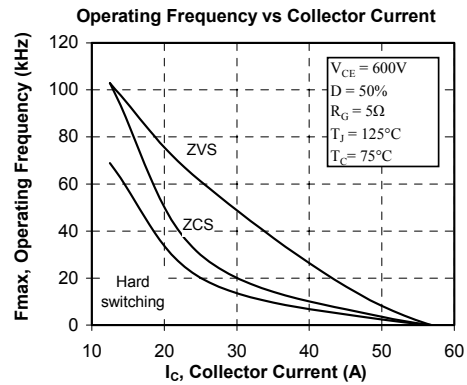
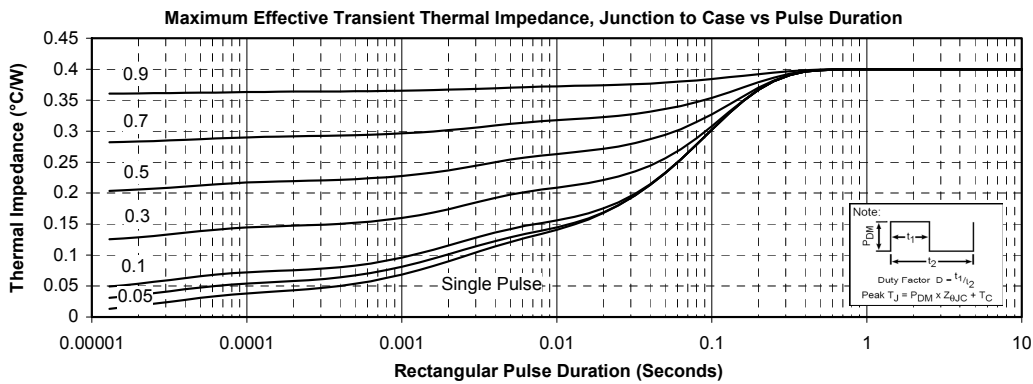
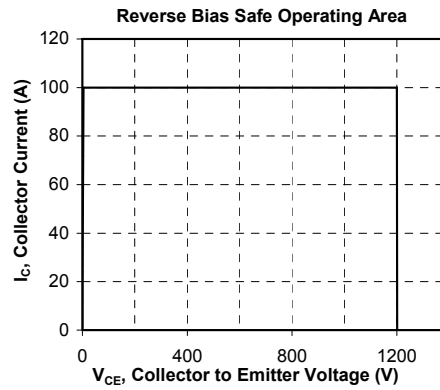
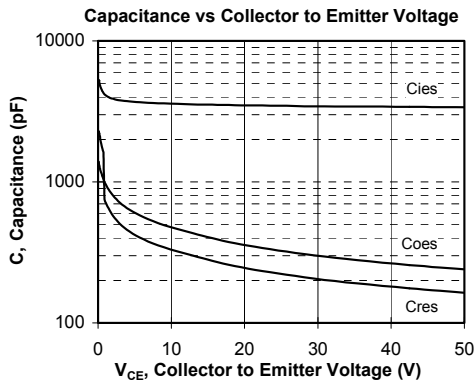


See application note 1901 - Mounting Instructions for SP3 Power Modules on [www.microsemi.com](http://www.microsemi.com)

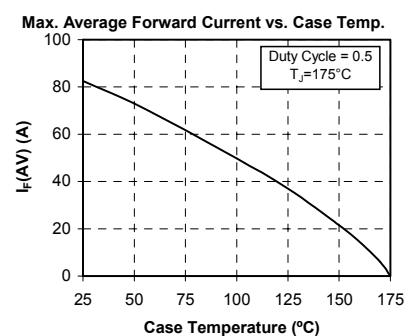
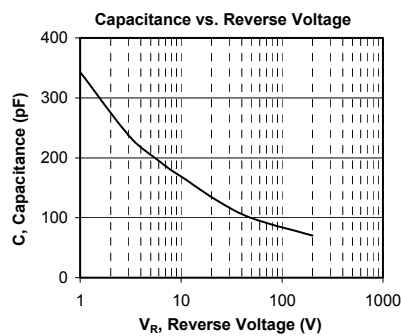
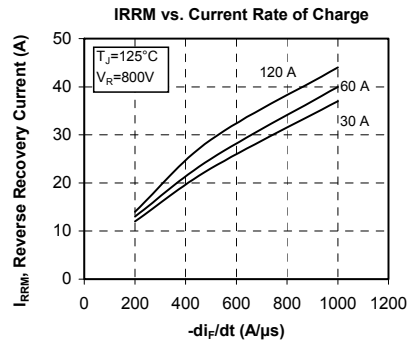
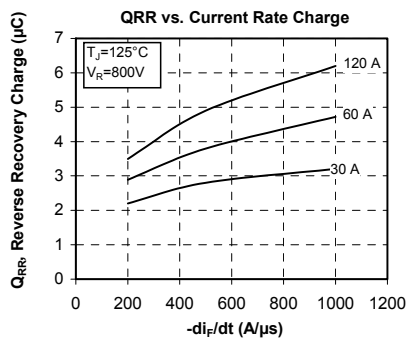
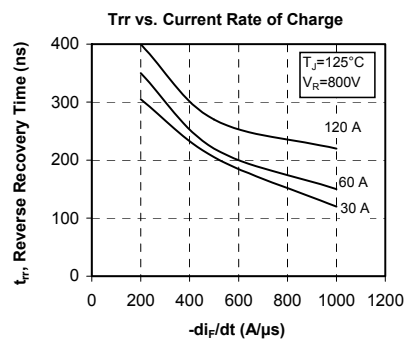
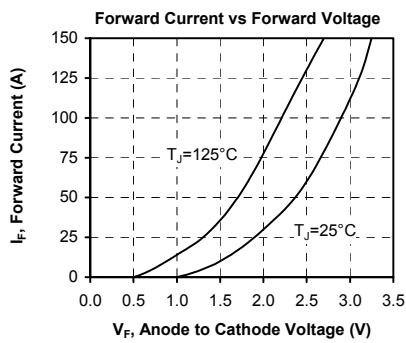
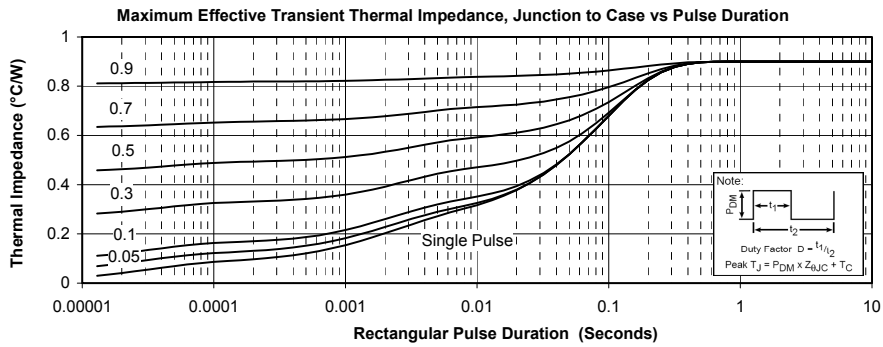
## Typical IGBT Performance Curve







## Typical diode Performance Curve



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